

Dual P-Channel 350V Enhancement Mode MOSFETs

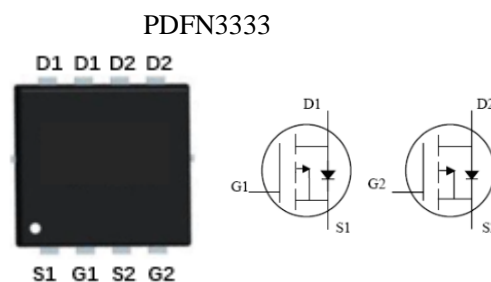
General Features

- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free available

V_{DSS}	$R_{DS(ON)}$ (Max.)	I_D
-350V	30 Ω	-0.5A

Applications

- High Efficiency SMPS
- Adaptor/Charger
- Active PFC



Ordering Information

Part Number	Package	Marking	Remark
FTF30P35D	PDFN3333	30P35D	Halogen Free

Absolute Maximum Ratings

 $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	FTF30P35D	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	-350	V
I_D	Continuous Drain Current	-0.5	A
I_{DM}	Pulsed Drain Current ^[2]	-2	
P_D	Power Dissipation	16	W
V_{GS}	Gate-to-Source Voltage	± 20	V
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^{\circ}\text{C}$
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	FTF30P35D	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	34	K/W

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-350	--	--	V	$V_{GS}=0V, I_D=-250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	-1	μA	$V_{DS}=-350V, V_{GS}=0V$
		--	--	-100	μA	$V_{DS}=-350V, V_{GS}=0V$ $T_J=125^\circ C$
I_{GSS}	Gate-to-Source Leakage Current	--	--	20	μA	$V_{GS}=+20V, V_{DS}=0V$
		--	--	-20		$V_{GS}=-20V, V_{DS}=0V$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	18	30	Ω	$V_{GS}=-10V, I_D=-200mA$ [3]
$V_{GS(TH)}$	Gate Threshold Voltage	-1	--	-3	V	$V_{GD}=0V, I_D=-250\mu A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	43.39	--	pF	$V_{GS}=0V$ $V_{DS}=-25V$ $f=1.0MHz$
C_{OSS}	Output Capacitance	--	6.94	--		
C_{RSS}	Reverse Transfer Capacitance	--	0.84	--		
$t_{d(ON)}$	Turn-on Delay Time	--	12	--	ns	$V_{GS} = -10V \sim 0V$ $V_{DD} = -25V, I_D = -80mA$ $R_G = 25\Omega$
t_{rise}	Rise Time	--	60	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	136	--		
t_{fall}	Fall Time	--	320	--		

Source-Drain Diode Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

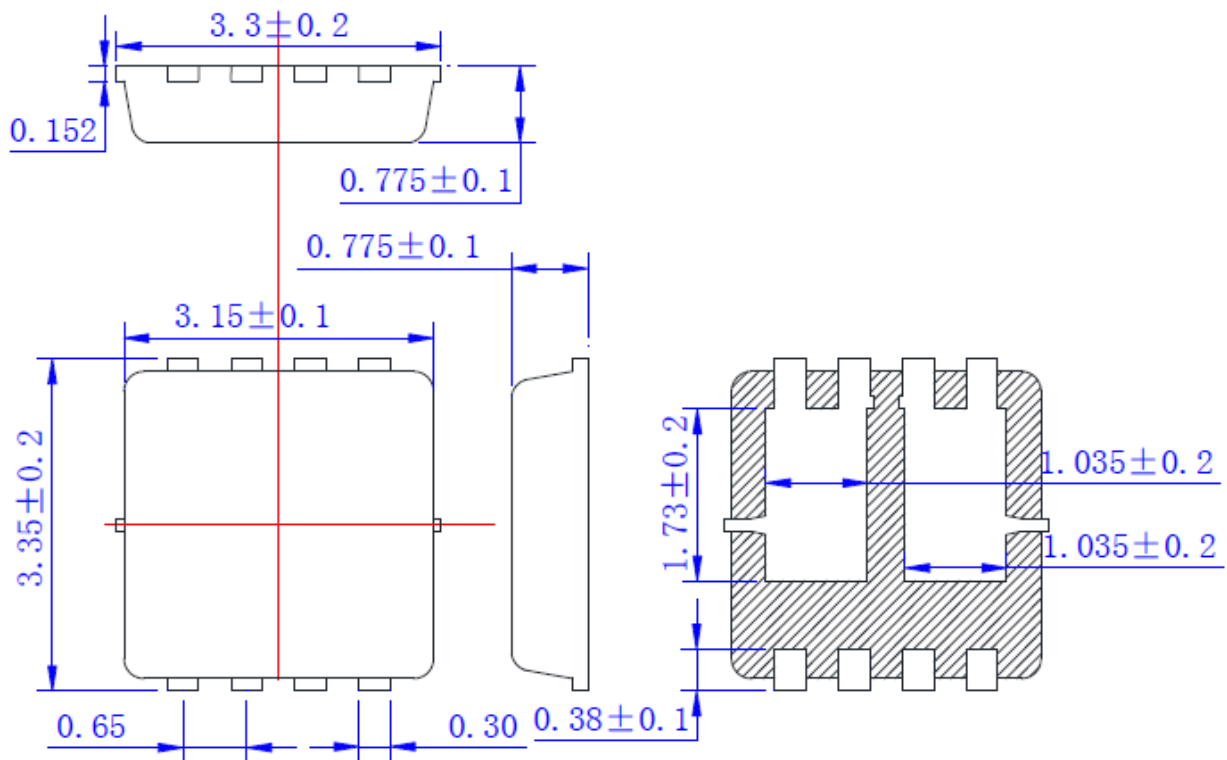
Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	-1.8	V	$I_{SD} = -200 mA, V_{GS} = 0 V$

NOTE:

 [1] $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$

[2] Repetitive rating, pulse width limited by maximum junction temperature.

 [3] Pulse width $\leq 380\mu s$; duty cycle $\leq 2\%$.

Package Dimensions
PDFN3333




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